

WW263 (NPN) & WW264 (PNP) Silicon Complementary Transistors Darlington Power Amplifier

Description:

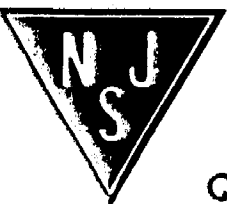
The WW263 (NPN) and WW264 (PNP) are complementary silicon Darlington power transistors in a TO220 type package designed for general purpose amplifier and low-speed switching applications.

Features:

- High DC Current Gain:
 $h_{FE} = 2500$ Typ (WW263)
 $h_{FE} = 3500$ Typ (WW264)
- Collector–Emitter Sustaining Voltage: $V_{CEO(sus)} = 100V$ Min
- Low Collector–Emitter Saturation Voltage:
 $V_{CE(sat)} = 2V$ Max @ $I_C = 5A$
- Monolithic Construction with Built–In Base–Emitter Shunt Resistor

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	100V
Collector–Base Voltage, V_{CB}	100V
Emitter–Base Voltage, V_{EB}	5V
Collector Current, I_C	
Continuous	10A
Peak	15A
Base Current, I_B	250mA
Total Power Dissipation ($T_C = +25^\circ C$), P_D	65W
Derate Above $25^\circ C$	0.52W/ $^\circ C$
Total Power Dissipation ($T_A = +25^\circ C$), P_D	2W
Derate Above $25^\circ C$	0.016W/ $^\circ C$
Operating Junction Temperature range, T_J	-65° to $+150^\circ C$
Storage Temperature range, T_{stg}	-65° to $+150^\circ C$
Thermal Resistance, Junction–to–Case, R_{thJC}	1.92 $^\circ C/W$
Thermal Resistance, Junction–to–Ambient, R_{thJA}	62.5 $^\circ C/W$



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Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 200\text{mA}, I_B = 0$, Note 1	100	-	-	V
Collector Cutoff Current	I_{CEO}	$V_{CE} = 100\text{V}, I_B = 0$	-	-	1.0	mA
		$V_{CE} = 100\text{V}, V_{EB(off)} = 1.5\text{V}$	-	-	300	μA
	I_{CEX}	$V_{CE} = 100\text{V}, V_{EB(off)} = 1.5\text{V}, T_C = +125^\circ\text{C}$	-	-	3	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}, I_C = 0$	-	-	5	mA
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	$I_C = 5\text{A}, V_{CE} = 3\text{V}$	1000	-	20000	
		$I_C = 10\text{A}, V_{CE} = 3\text{V}$	100	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 0.01\text{A}$	-	-	2	V
		$I_C = 10\text{A}, I_B = 0.1\text{A}$	-	-	3	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$I_C = 3\text{A}, V_{CE} = 3\text{V}$	-	-	2.8	V
		$I_C = 10\text{A}, V_{CE} = 3\text{V}$	-	-	4.5	V
Dynamic Characteristics						
Small-Signal Current Gain	$ h_{fe} $	$I_C = 1\text{A}, V_{CE} = 5\text{V}, f_{test} = 1\text{MHz}$	20	-	-	
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	-	200	pF
Small-Signal Current Gain	h_{fe}	$I_C = 1\text{A}, V_{CE} = 5\text{V}, f = 1\text{kHz}$	1000	-	-	

Note 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

